Low Noise High Efficiency 3.75 µm and 2.8 µm Global Shutter CMOS Pixel Arrays

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Aptina Global Shutter Pixel Development



2000200520102013Trend of reducing GS pixel size while preserving sensor performance.

1st Gen [1], 2nd Gen [2], and 3rd Gen [3] GS pixels.





6T GS Pixel with true CDS (4T effective in a 2-way CEPA architecture).



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3rd Gen Global Shutter Efficiency Improvement. Buried Light Shield.





3rd Gen 3.75µm GS Pixel vs. 2nd Gen 6.0µm GS Pixel Temporal SNR.





Pump Gate Concept for Clocked Charge Transfer from PD to SN. No limitations on PD, SN, and FD potential budgets.





Charge Acquisition





1st Pump Transfer Beginning





1st Pump Transfer Transitioning





1st Pump Transfer Complete









2nd Pump Transfer Complete









Nth Pump Transfer Complete







4th and 3rd Gen 3.75µm Global Shutter vs. ERS Pixel Total SNR.



Table 1

	Unit	Gen2 [2]	Gen3 [3]	Gen3	Gen4		Note
Pixel Pitch	um	6	3.75	3.75	3.75	2.8	
True CDS		No	Yes	Yes	Yes	Yes	
Max Quantum Efficiency	%	58	70	70	75	70	mono
Linear Full-well	Ke-	17.5	7.5	7.5	> 15	> 12	
Pixel Response Non-uniformity	%	0.7	0.8	0.8	0.6	0.6	50% signal
Pixel Total Noise Floor	e-	25	8	8	3	3	25C Tj
Storage Dark Current	e-/sec	3000	2000	2000	90	60	60C Tj
Global Shutter Efficiency	ratio	1700	310	2000	3000	2200	average

Comparison of Global Shutter Pixel Generations.



ERS vs. GS Image Performance



Image of the rotating fan taken with GS and RS sensors: a. 1Mpix sensor, 3.75µm rolling shutter pixel b. 1Mpix sensor, 3.75µm global shutter pixel

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Conclusion

- We successfully demonstrated 4th generation of global shutter (GS) pixels utilizing pump charge transfer method.
- 4th generation implemented into 3.75µm and 2.8µm GS pixels with significant improvements in dark current, noise floor, dynamic range, and global shutter efficiency.
- 4th generation 2.8µm GS pixel, to our knowledge, is the smallest published CMOS GS pixel with true CDS.
- 4th generation architecture opens further pixel shrinking and extension of applications range.
- 3rd generation of 3.75µm GS pixel demonstrated significant improvement of global shutter efficiency.



References

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